



# Bipolar PNP Bare Die – BTP6035

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## Part Description

The BTP6035 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

## Key Parameters:

- VCBO = -180V
- VCEO = -140V
- VEBO = -6V
- hFE = 100-300 @ VCE = -5V, IC = -1A
- VCE(Sat) = -0.37V @ IC = -3A, IB = -300mA
- fT = 100 MHz @ VCE = -10V, IE = 0A
- COBO = 40pF @ VCB = -20V

## Features

Very Low VCE(sat). Designed to provide performance equivalent to ZETEX / DIODES INC. FZT955

## Die Size (Unawn)

1640 $\mu$ m X 1640 $\mu$ m, 65 Mils X 65 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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